
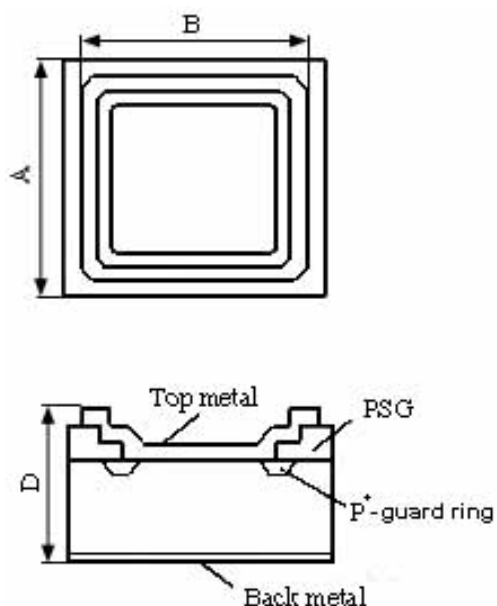


# SCHOTTKY DIODES KDS 2130B. PRELIMINARY



Rev.1. Feb. 2010

 <b>VSP-MIKRON</b>	<b>3A/25V. Die Size-65mil.</b>			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	28	31
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25°C, $I_F=3,0A$	$V_F$	V	0,38	0,36 (0,34-typ)
Maximum Reverse Current @ 25°C, $V_R=25V$ 25°C, $V_R=28V$ 100°C, $V_R=25V$	$I_R$	mA	0,8 - 50,0	0,5 0,8 45,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	110	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<125°C$ .	$I_{RRM}$	A	2,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	125	



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	1650 1650
$B_x$ $B_y$	Top Metal Size	1470 1470
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.  
*Backside metal:* **Ti-Ni-Ag**.